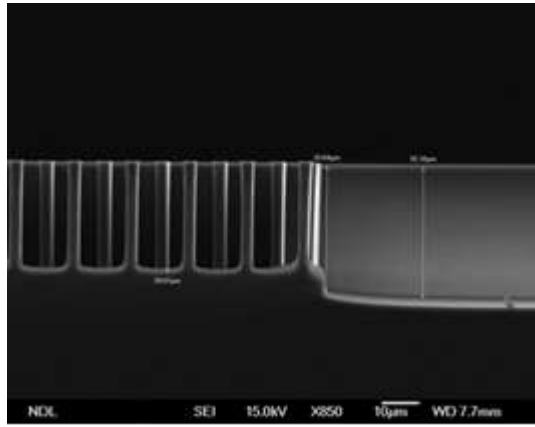
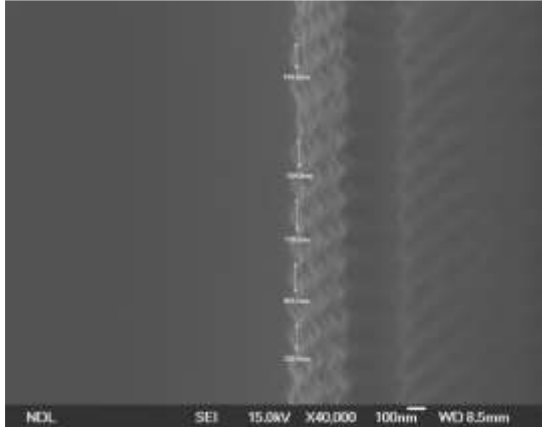


# 感應耦合式電漿蝕刻系統

(Inductive Couple Plasma Etcher, ICP Etcher)

## 標準製程 (Standard Recipes)

### • HAR (High Aspect Ratio) recipe:

Etch Rate	~0.5um/loop
Selectivity to I-line	PR ~50:1
Etch Profile	>85°
Aspect Ratio	> 10:1
	

### • ISO (Isotropic) Recipe

Etch Rate	~5um/min
Selectivity to Oxide	>50:1
Etch Profile	Isotropic Si etch